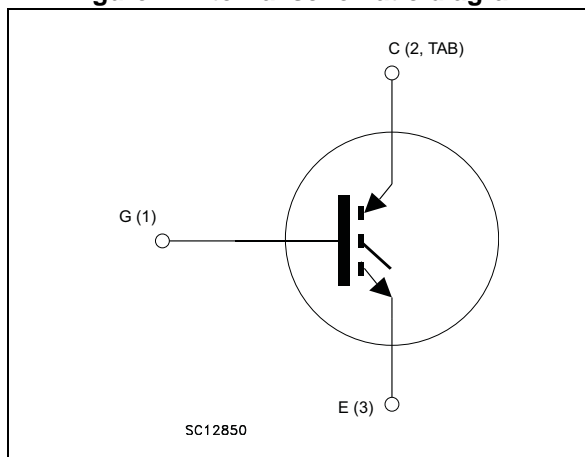


Figure 1. Internal schematic diagram



Features

- Maximum junction temperature: $T_J = 175\text{ }^\circ\text{C}$
- Tail-less switching off
- $V_{CE(sat)} = 1.85\text{ V (typ.) @ } I_C = 30\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance

Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- Very high frequency converters

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the V series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, a positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1. Device summary

| Order codes | Marking | Package | Packaging |
|-------------|-----------|---------|-----------|
| STGFW30V60F | GFW30V60F | TO-3PF | Tube |
| STGW30V60F | GW30V60F | TO-247 | Tube |
| STGWT30V60F | GWT30V60F | TO-3P | Tube |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | | Unit |
|----------------|---|-----------------|--------------------|------|
| | | TO-3P TO-247 | TO-3PF | |
| V_{CES} | Collector-emitter voltage ($V_{GE} = 0$) | 600 | | V |
| I_C | Continuous collector current at $T_C = 25\text{ °C}$ | 60 | 60 ⁽¹⁾ | A |
| I_C | Continuous collector current at $T_C = 100\text{ °C}$ | 30 | 30 ⁽¹⁾ | A |
| $I_{CP}^{(2)}$ | Pulsed collector current | 120 | 120 ⁽¹⁾ | A |
| V_{GE} | Gate-emitter voltage | ±20 | | V |
| P_{TOT} | Total dissipation at $T_C = 25\text{ °C}$ | 260 | 58 | W |
| V_{ISO} | Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ °C}$) | | 3.5 | kV |
| T_{STG} | Storage temperature range | - 55 to 150 | | °C |
| T_J | Operating junction temperature | - 55 to 175 | | °C |

1. Limited by maximum junction temperature.
2. Pulse width limited by maximum junction temperature.

Table 3. Thermal data

| Symbol | Parameter | Value | | Unit |
|------------|-------------------------------------|-----------------|--------|------|
| | | TO-3P TO-247 | TO-3PF | |
| R_{thJC} | Thermal resistance junction-case | 0.58 | 2.6 | °C/W |
| R_{thJA} | Thermal resistance junction-ambient | 50 | | °C/W |

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|------|---------------|
| $V_{(BR)CES}$ | Collector-emitter breakdown voltage ($V_{GE} = 0$) | $I_C = 2\text{ mA}$ | 600 | | | V |
| $V_{CE(sat)}$ | Collector-emitter saturation voltage | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ | | 1.85 | 2.3 | V |
| | | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $T_J = 125\text{ °C}$ | | 2.15 | | |
| | | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $T_J = 175\text{ °C}$ | | 2.35 | | |
| $V_{GE(th)}$ | Gate threshold voltage | $V_{CE} = V_{GE}, I_C = 1\text{ mA}$ | 5 | 6 | 7 | V |
| I_{CES} | Collector cut-off current ($V_{GE} = 0$) | $V_{CE} = 600\text{ V}$ | | | 25 | μA |
| I_{GES} | Gate-emitter leakage current ($V_{CE} = 0$) | $V_{GE} = \pm 20\text{ V}$ | | | 250 | nA |

Table 5. Dynamic characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|--|------|------|------|------|
| C_{ies} | Input capacitance | $V_{CE} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GE} = 0$ | - | 3750 | - | pF |
| C_{oes} | Output capacitance | | - | 120 | - | pF |
| C_{res} | Reverse transfer capacitance | | - | 77 | - | pF |
| Q_g | Total gate charge | $V_{CC} = 480\text{ V}, I_C = 30\text{ A},$ $V_{GE} = 15\text{ V},$ see Figure 26 | - | 163 | - | nC |
| Q_{ge} | Gate-emitter charge | | - | 28 | - | nC |
| Q_{gc} | Gate-collector charge | | - | 72 | - | nC |

Table 6. IGBT switching characteristics (inductive load)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|---------------------------|---|------|------|---------|------------|
| $t_{d(on)}$ | Turn-on delay time | $V_{CE} = 400\text{ V}$, $I_C = 30\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, see Figure 25 | - | 45 | - | ns |
| t_r | Current rise time | | - | 16 | - | ns |
| $(di/dt)_{on}$ | Turn-on current slope | | - | 1500 | - | A/ μ s |
| $t_{d(off)}$ | Turn-off delay time | | - | 189 | - | ns |
| t_f | Current fall time | | - | 19 | - | ns |
| $E_{on}^{(1)}$ | Turn-on switching losses | | - | 383 | - | μ J |
| $E_{off}^{(2)}$ | Turn-off switching losses | | - | 233 | - | μ J |
| E_{ts} | Total switching losses | - | 616 | - | μ J | |
| $t_{d(on)}$ | Turn-on delay time | $V_{CE} = 400\text{ V}$, $I_C = 30\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$, see Figure 25 | - | 42 | - | ns |
| t_r | Current rise time | | - | 17 | - | ns |
| $(di/dt)_{on}$ | Turn-on current slope | | - | 1337 | - | A/ μ s |
| $t_{d(off)}$ | Turn-off delay time | | - | 193 | - | ns |
| t_f | Current fall time | | - | 32 | - | ns |
| $E_{on}^{(1)}$ | Turn-on switching losses | | - | 794 | - | μ J |
| $E_{off}^{(2)}$ | Turn-off switching losses | | - | 378 | - | μ J |
| E_{ts} | Total switching losses | - | 1172 | - | μ J | |

1. Energy losses include reverse recovery of the external diode. The diode is the same of the copacked STGW30V60DF.
2. Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature for TO-247 and TO-3P

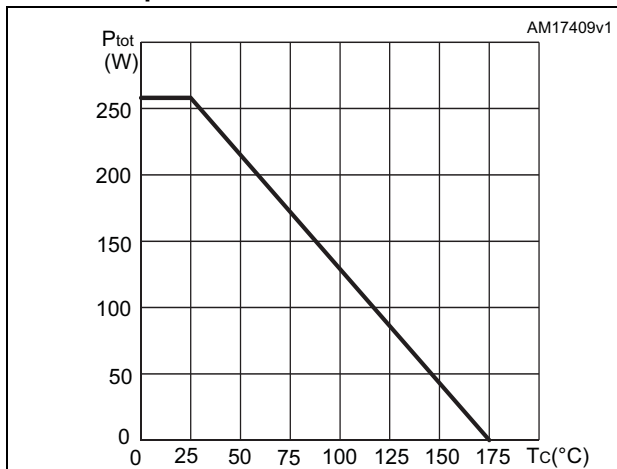


Figure 3. Collector current vs. case temperature for TO-247 and TO-3P

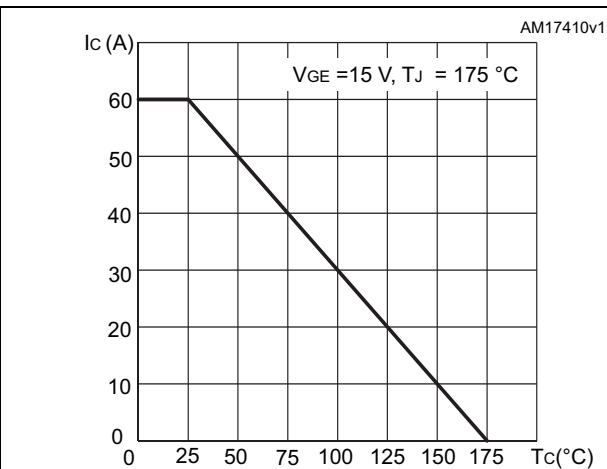


Figure 4. Power dissipation vs. case temperature for TO-3PF

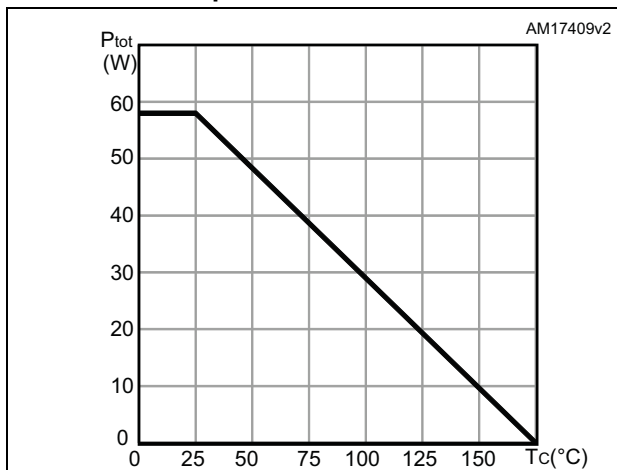


Figure 5. Collector current vs. case temperature for TO-3PF

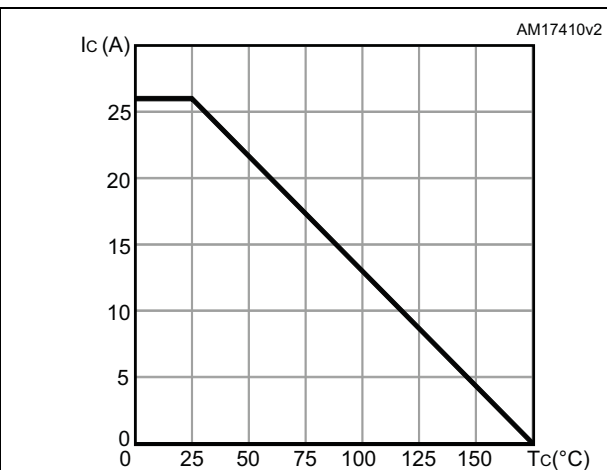


Figure 6. Output characteristics (T_J=25°C)

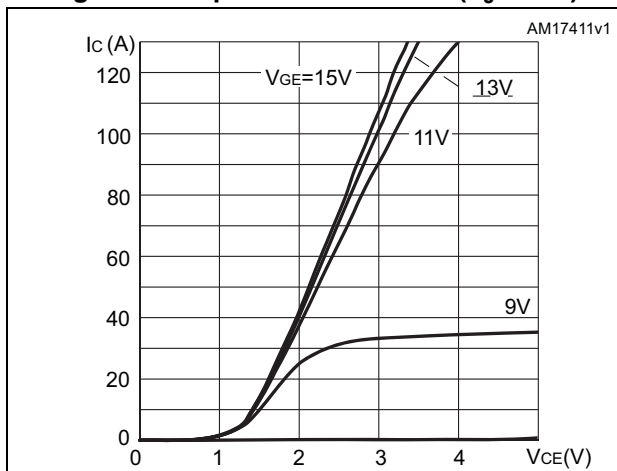


Figure 7. Output characteristics (T_J=175°C)

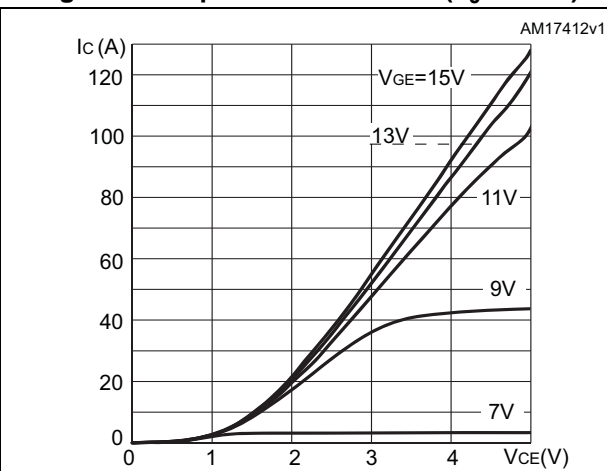


Figure 8. $V_{CE(sat)}$ vs. junction temperature

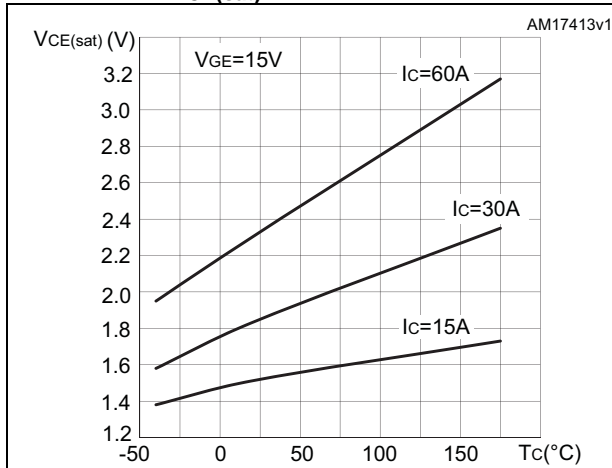


Figure 9. $V_{CE(sat)}$ vs. collector current

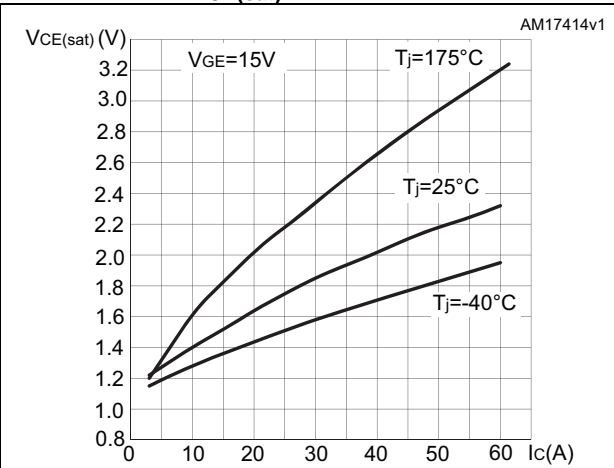


Figure 10. Safe operating area for TO-3PF

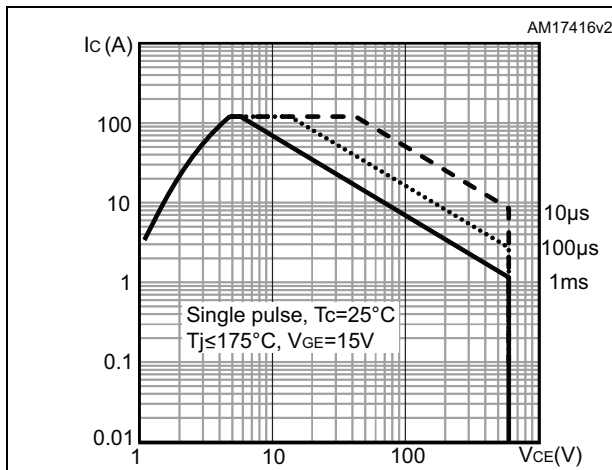


Figure 11. Safe operating area for TO-247 and TO-3P

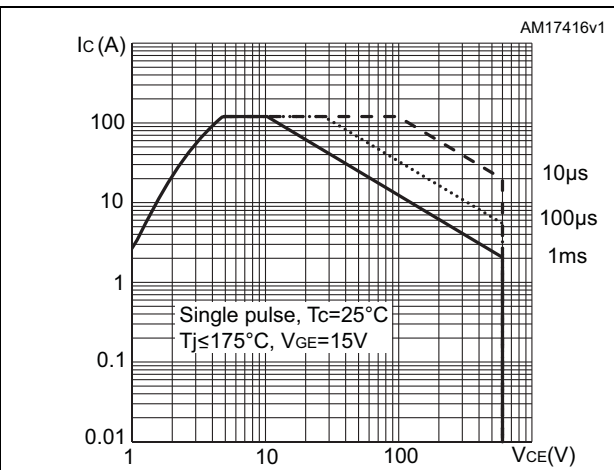


Figure 12. Normalized $V_{GE(th)}$ vs junction temperature

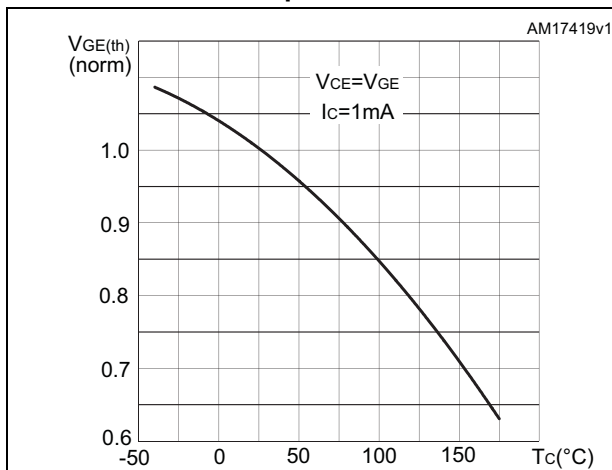


Figure 13. Normalized $V_{(BR)CES}$ vs. junction temperature

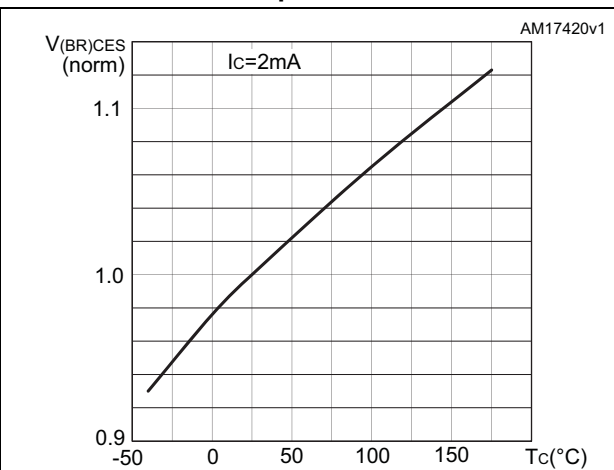


Figure 14. Capacitance variations

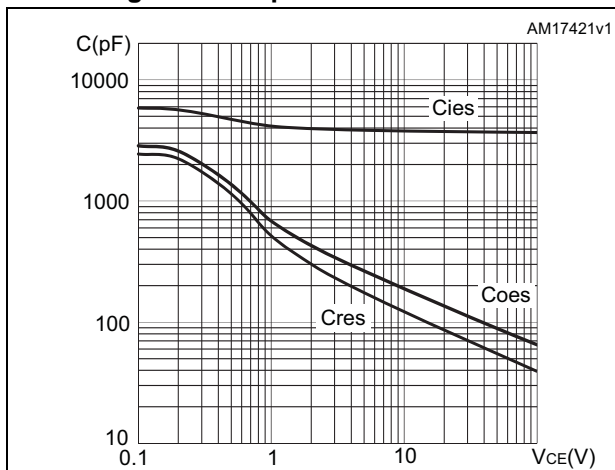


Figure 15. Gate charge vs. gate-emitter voltage

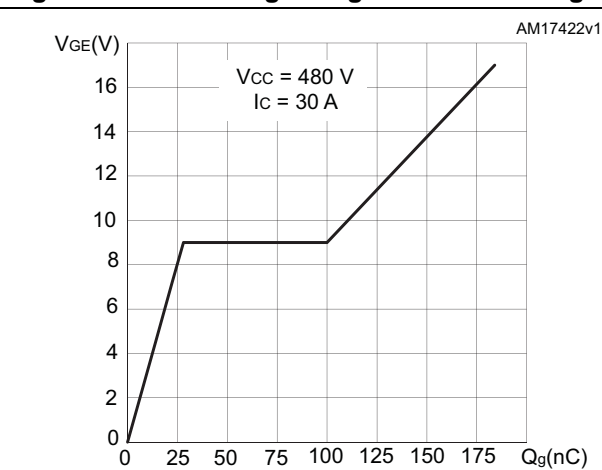


Figure 16. Switching losses vs. collector current

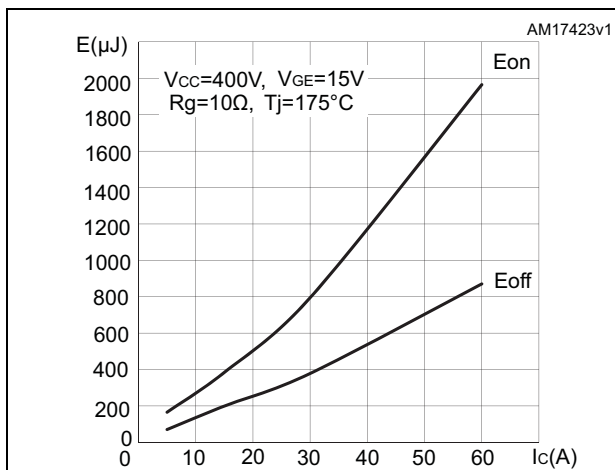


Figure 17. Switching losses vs. gate resistance

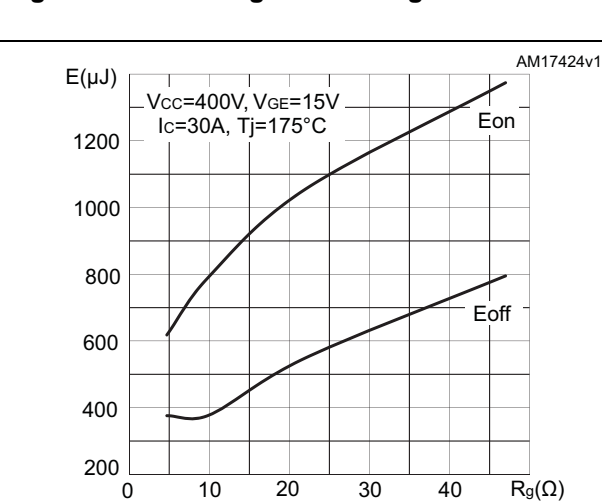


Figure 18. Switching losses vs. junction temperature

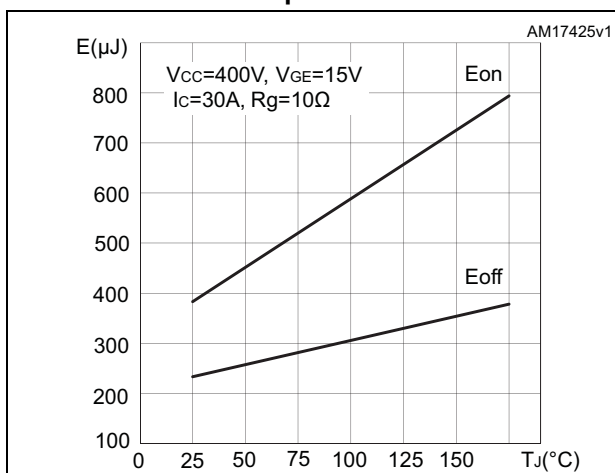


Figure 19. Switching losses vs. collector emitter voltage

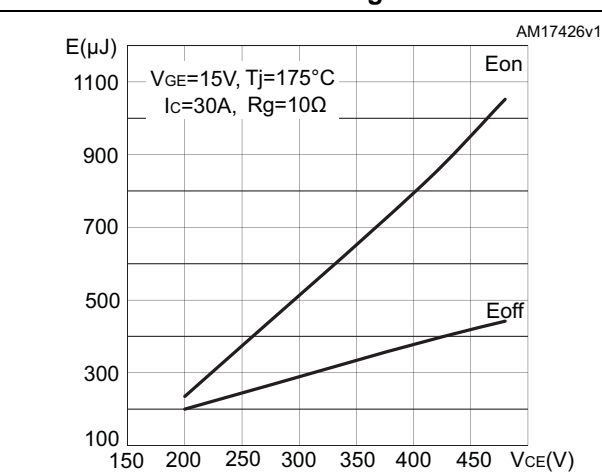


Figure 20. Switching times vs. collector current

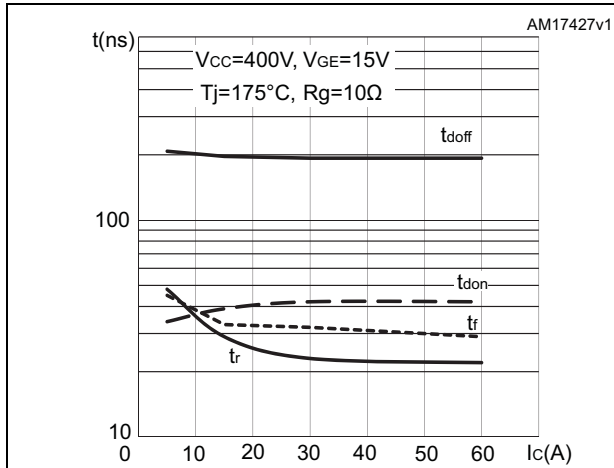


Figure 21. Switching times vs. gate resistance

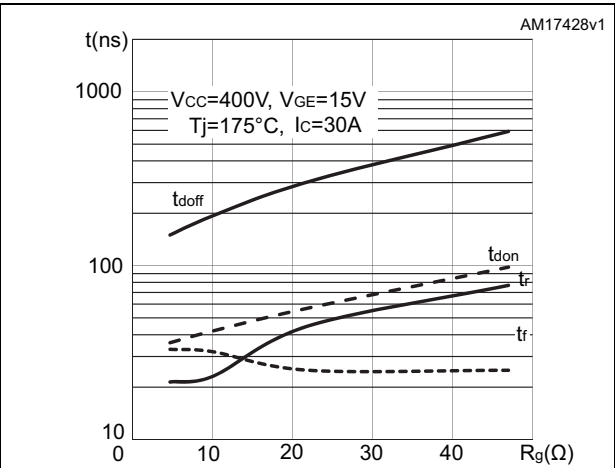


Figure 22. Transfer characteristics

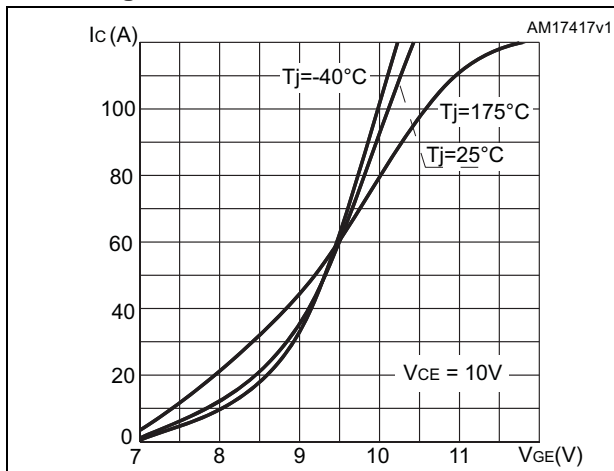


Figure 23. Thermal data for TO-3PF

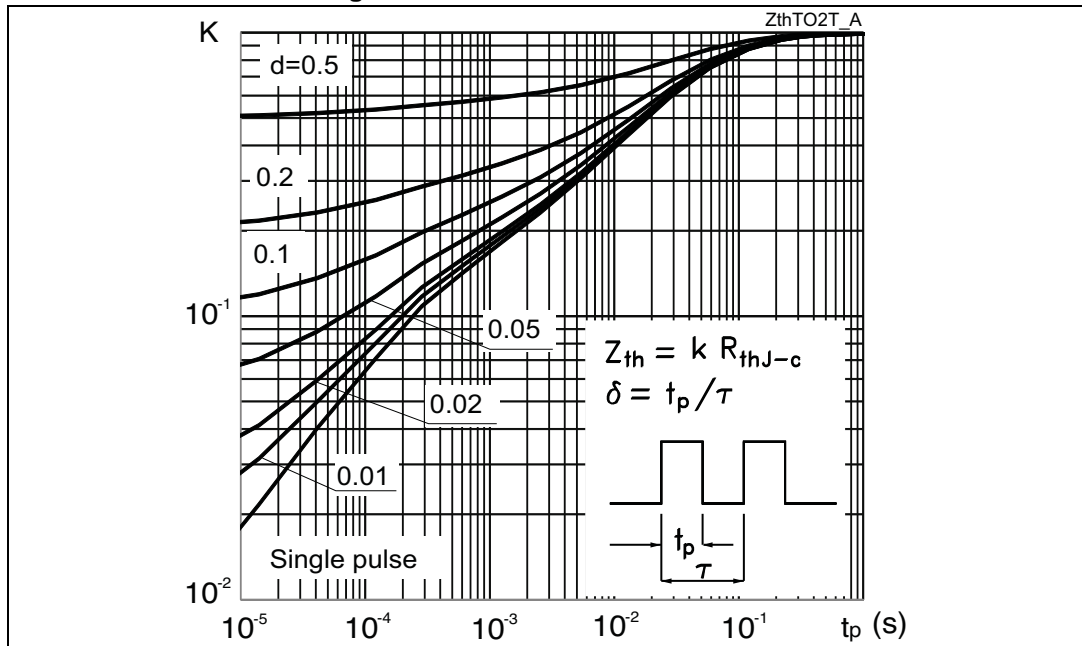
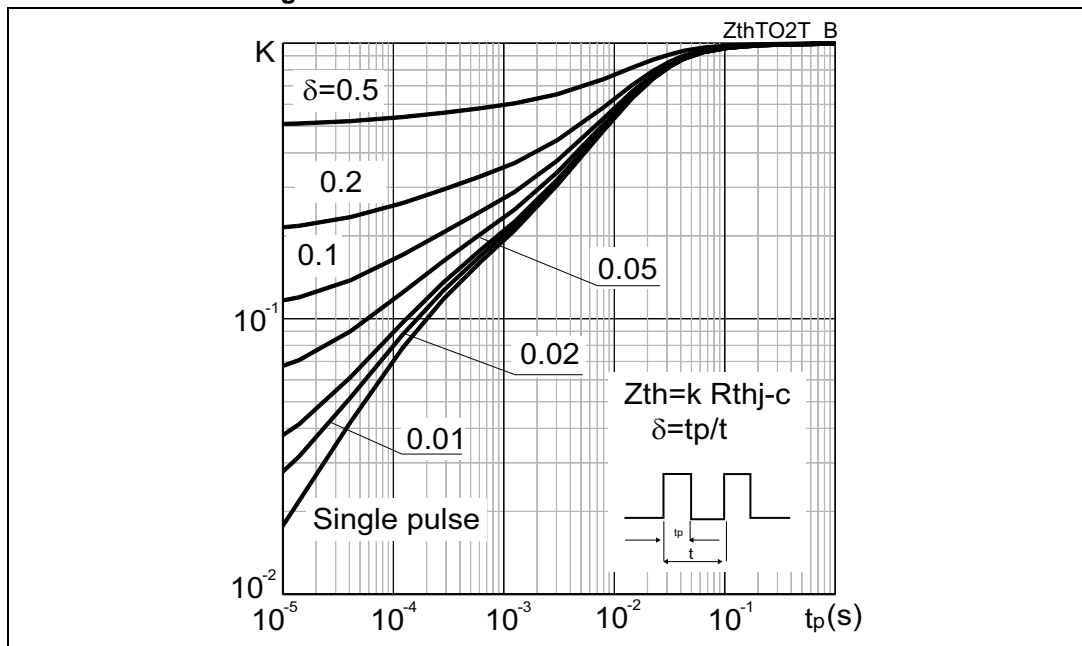


Figure 24. Thermal data for TO-3P and TO-247



3 Test circuits

Figure 25. Test circuit for inductive load switching

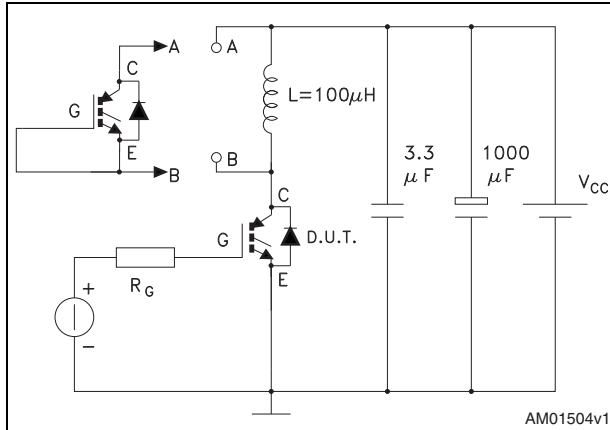


Figure 26. Gate charge test circuit

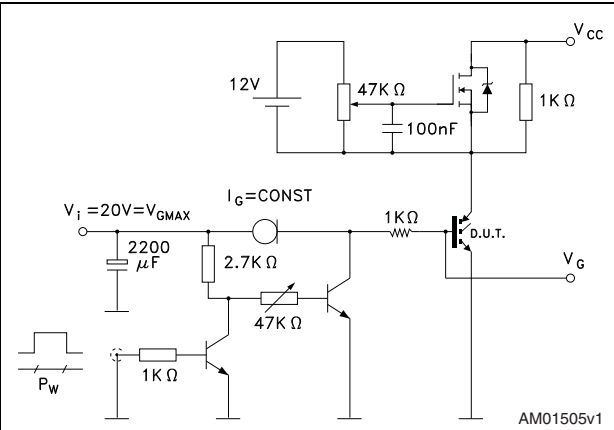
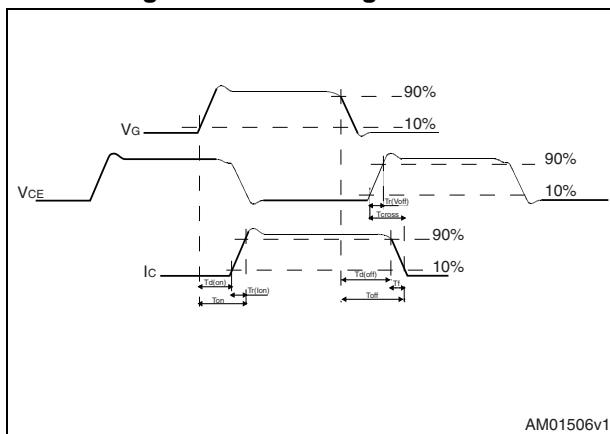


Figure 27. Switching waveform

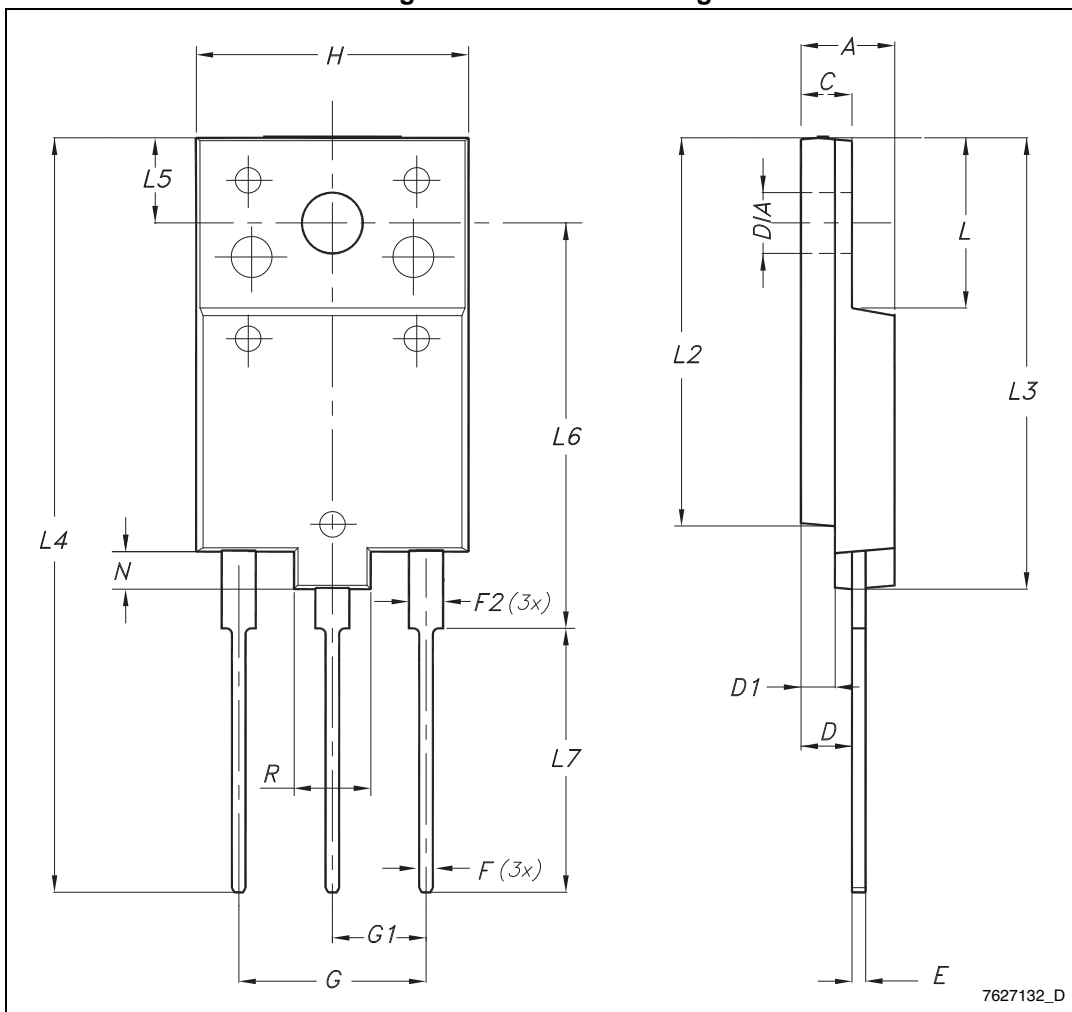


4 Package mechanical data

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4.1 TO-3PF, STGFW30V60F

Figure 28. TO-3PF drawing



7627132_D

Table 7. TO-3PF mechanical data

| Dim. | mm | | |
|------|-------|------|-------|
| | Min. | Typ. | Max. |
| A | 5.30 | | 5.70 |
| C | 2.80 | | 3.20 |
| D | 3.10 | | 3.50 |
| D1 | 1.80 | | 2.20 |
| E | 0.80 | | 1.10 |
| F | 0.65 | | 0.95 |
| F2 | 1.80 | | 2.20 |
| G | 10.30 | | 11.50 |
| G1 | | 5.45 | |
| H | 15.30 | | 15.70 |
| L | 9.80 | 10 | 10.20 |
| L2 | 22.80 | | 23.20 |
| L3 | 26.30 | | 26.70 |
| L4 | 43.20 | | 44.40 |
| L5 | 4.30 | | 4.70 |
| L6 | 24.30 | | 24.70 |
| L7 | 14.60 | | 15 |
| N | 1.80 | | 2.20 |
| R | 3.80 | | 4.20 |
| Dia | 3.40 | | 3.80 |

4.2 TO-247, STGW30V60F

Figure 29. TO-247 drawing

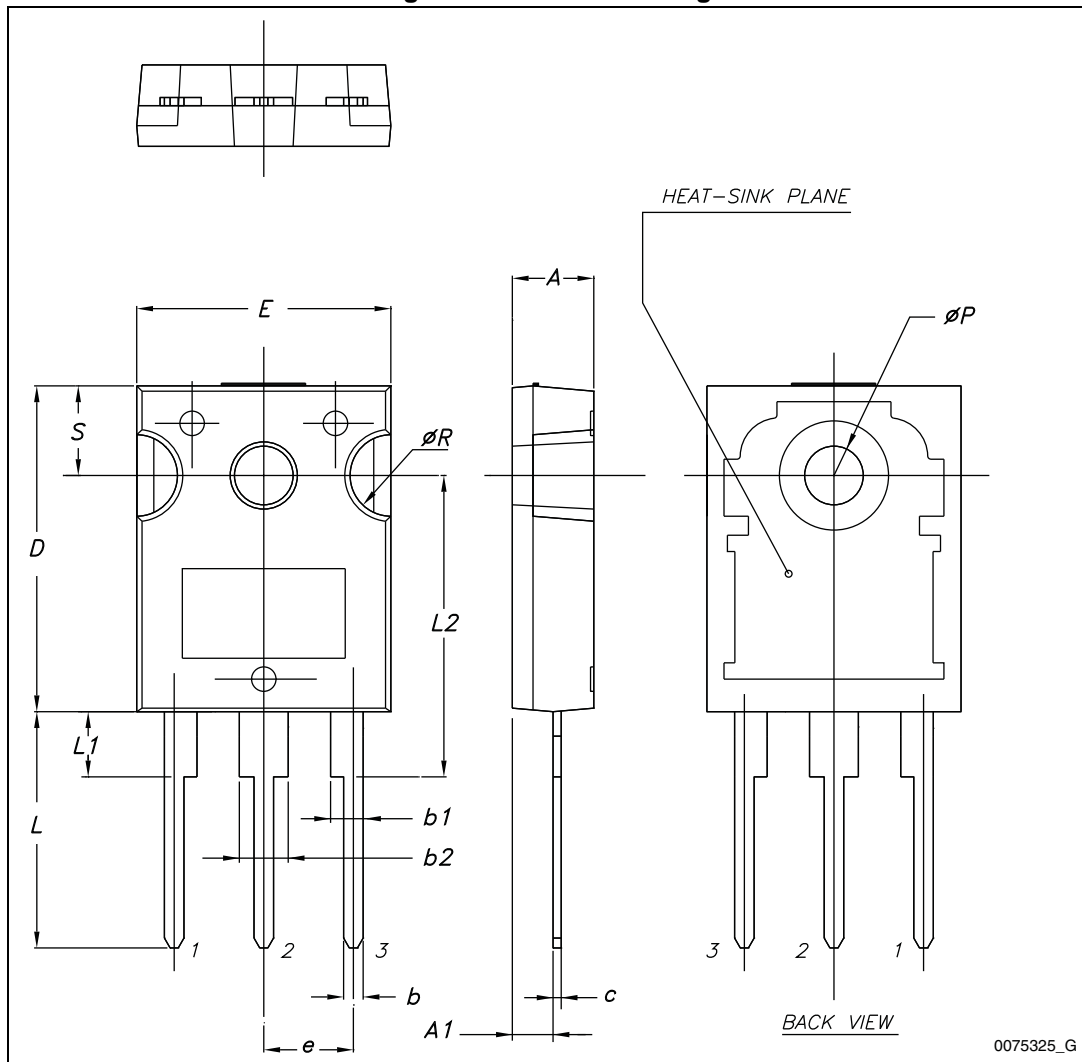


Table 8. TO-247 mechanical data

| Dim. | mm. | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.85 | | 5.15 |
| A1 | 2.20 | | 2.60 |
| b | 1.0 | | 1.40 |
| b1 | 2.0 | | 2.40 |
| b2 | 3.0 | | 3.40 |
| c | 0.40 | | 0.80 |
| D | 19.85 | | 20.15 |
| E | 15.45 | | 15.75 |
| e | 5.30 | 5.45 | 5.60 |
| L | 14.20 | | 14.80 |
| L1 | 3.70 | | 4.30 |
| L2 | | 18.50 | |
| ØP | 3.55 | | 3.65 |
| ØR | 4.50 | | 5.50 |
| S | 5.30 | 5.50 | 5.70 |

4.3 TO-3P, STGWT30V60F

Figure 30. TO-3P drawing

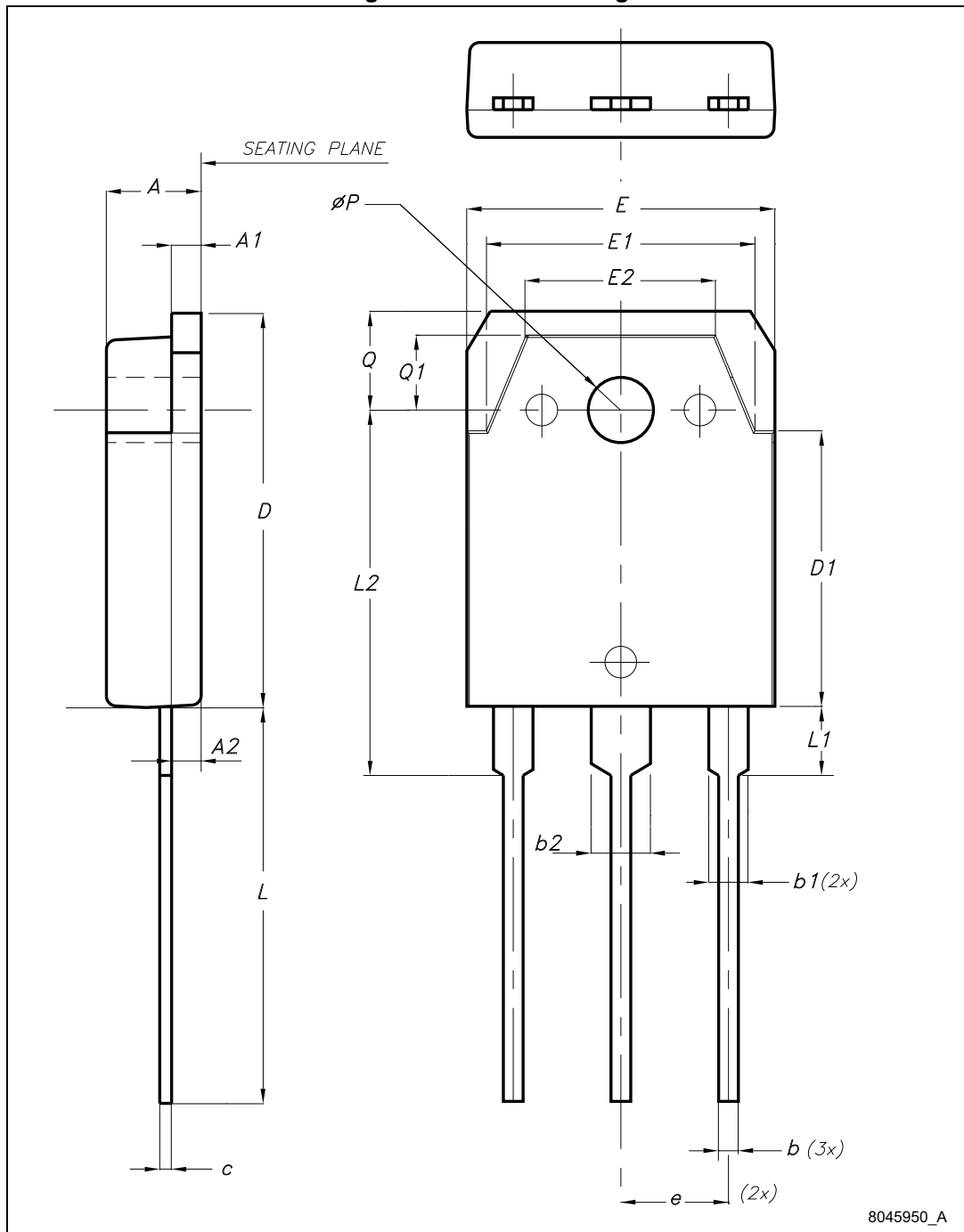


Table 9. TO-3P mechanical data

| Dim. | mm | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.60 | | 5 |
| A1 | 1.45 | 1.50 | 1.65 |
| A2 | 1.20 | 1.40 | 1.60 |
| b | 0.80 | 1 | 1.20 |
| b1 | 1.80 | | 2.20 |
| b2 | 2.80 | | 3.20 |
| c | 0.55 | 0.60 | 0.75 |
| D | 19.70 | 19.90 | 20.10 |
| D1 | | 13.90 | |
| E | 15.40 | | 15.80 |
| E1 | | 13.60 | |
| E2 | | 9.60 | |
| e | 5.15 | 5.45 | 5.75 |
| L | 19.50 | 20 | 20.50 |
| L1 | | 3.50 | |
| L2 | 18.20 | 18.40 | 18.60 |
| øP | 3.10 | | 3.30 |
| Q | | 5 | |
| Q1 | | 3.80 | |

5 Revision history

Table 10. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 24-Jul-2013 | 1 | Initial release. |
| 29-Jul-2013 | 2 | Updated Table 1: Device summary . |
| 08-Oct-2013 | 3 | Updated title, features and description in cover page. |
| 08-Apr-2014 | 4 | Updated Table 4: Static characteristics and Section 4: Package mechanical data . |

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